



**UNIVERSITÉ  
DE GENÈVE**

**FACULTÉ DES SCIENCES**  
Département de physique  
nucléaire et corpusculaire



**erc**  
European Research Council  
Established by the European Commission

# **MONOLITH** - Picosecond Time Stamping in Fully Monolithic Highly- granular Pixel Sensor

Matteo Milanesio on behalf of the MONOLITH team

University of Geneva

[Joint Annual Meeting of SPS and ÖPG, 4 - 8 September 2023 in Basel](#)

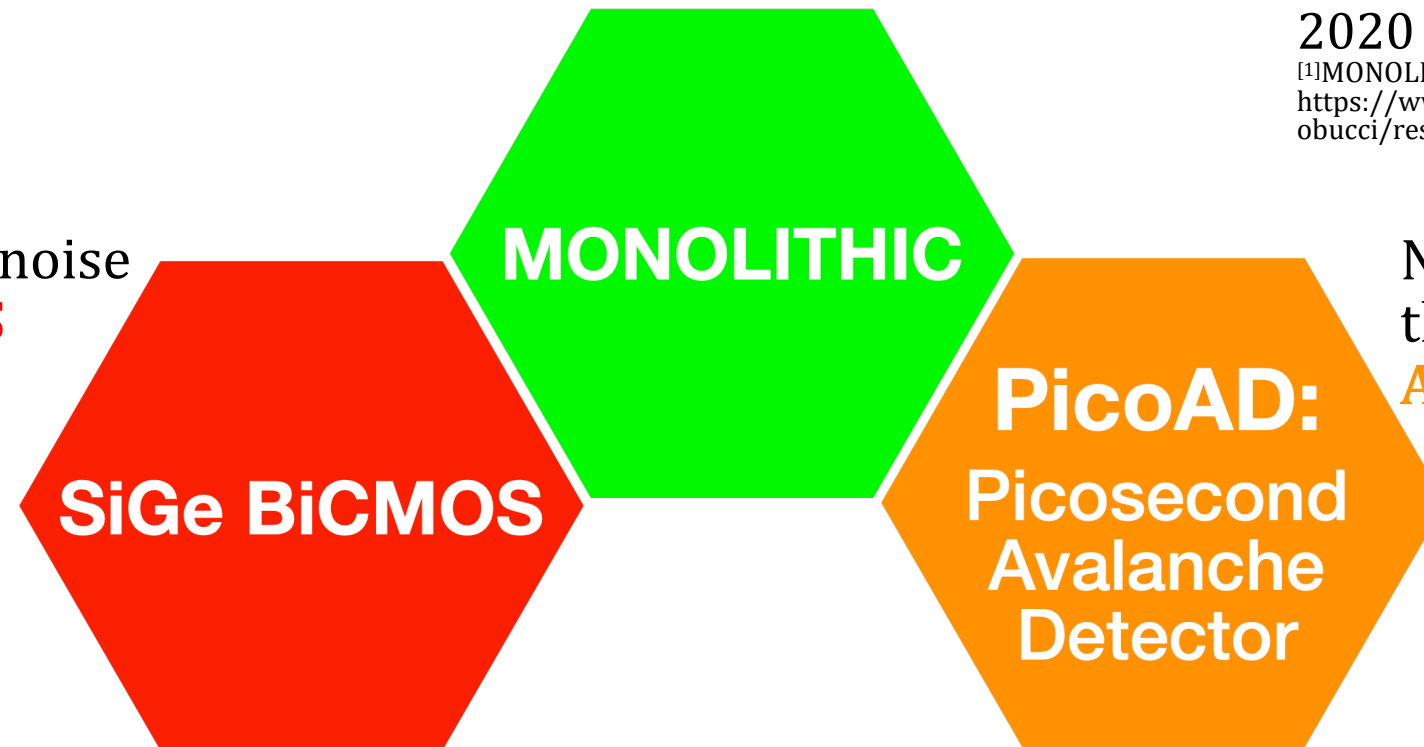
## Monolithic silicon sensor able to:

- measure precisely the 3D spatial position of charged particles
- provide picosecond time resolution

Funded by the H2020 ERC  
Advanced grant 884447<sup>[1]</sup>, July  
2020 - June 2025

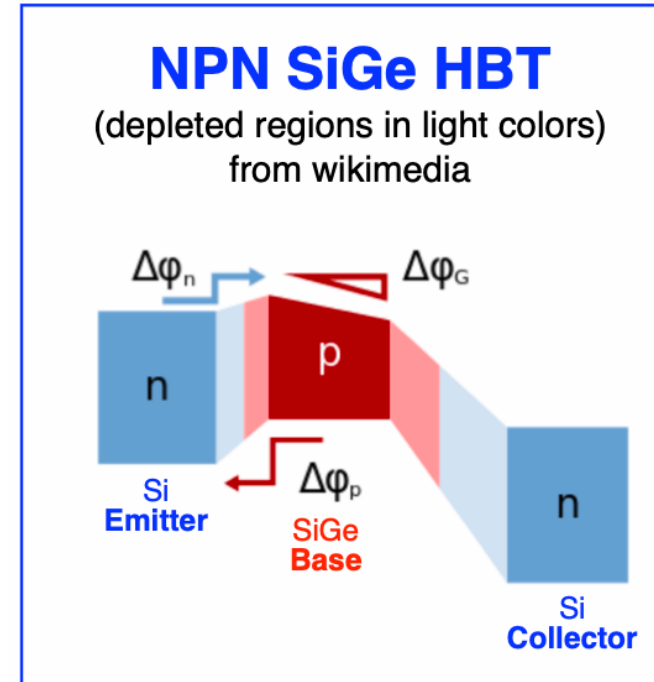
<sup>[1]</sup>MONOLITH H2020 ERC Advanced Project Web Page -  
<https://www.unige.ch/dpnc/en/groups/giuseppe-iac-obucci/research/monolith-erc-advanced-project/>

Fast and low-noise  
**SiGe BiCMOS**  
electronics



Novel sensor concept,  
the **Picosecond  
Avalanche Detector**®

- SiGe HBT = BJT with Germanium as base material:
  - higher doping in base possible
  - thinner base
  - **reduced base resistance  $R_b$**
- Grading of Ge doping in base:
  - charge transport in base via drift
  - reduced charge transit time in base
  - **high current gain  $\beta$**



$$ENC_{series\ noise} \propto \sqrt{k_1 \frac{C_{tot}^2}{\beta} + k_2 R_b C_{tot}^2} \rightarrow \sigma_{jitter} = \frac{\sigma_V}{\frac{dV}{dt}} \approx ENC * Rise\ Time$$



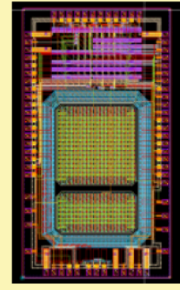
Leading-edge **IHP SG13G2** technology: **130 nm** process featuring **SiGe HBT**

# Monolithic SiGe BiCMOS prototypes



## NO GAIN LAYER

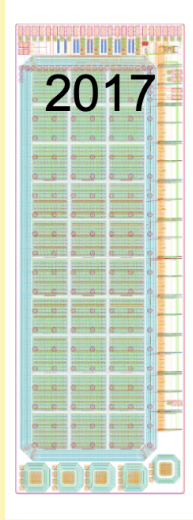
2016



**200 ps**

- 1 mm<sup>2</sup> pixel
- Discriminator

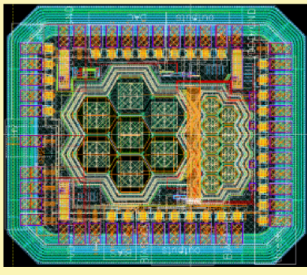
2017



**110 ps**

- 30 pixels 500x500μm<sup>2</sup>
- 100ps TDC +I/O logic

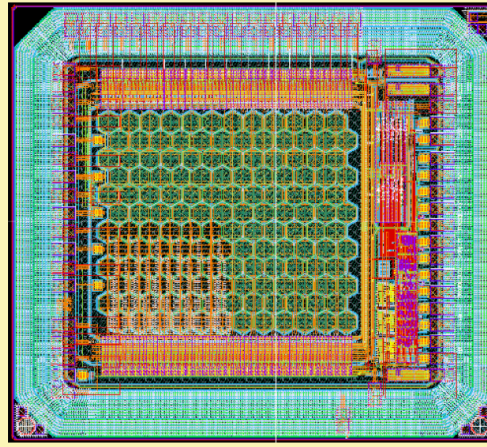
2018



**50 ps**

- Hexagonal pixels 65μm and 130μm side
- Discriminator output

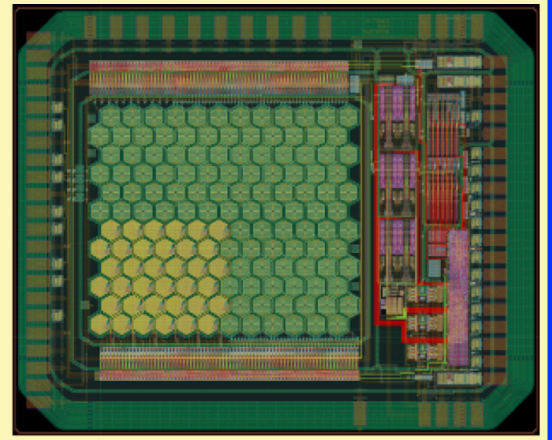
2019



**36 ps**

- Hexagonal pixels 65μm side
- 30ps TDC +I/O logic
- Analog channels

2022



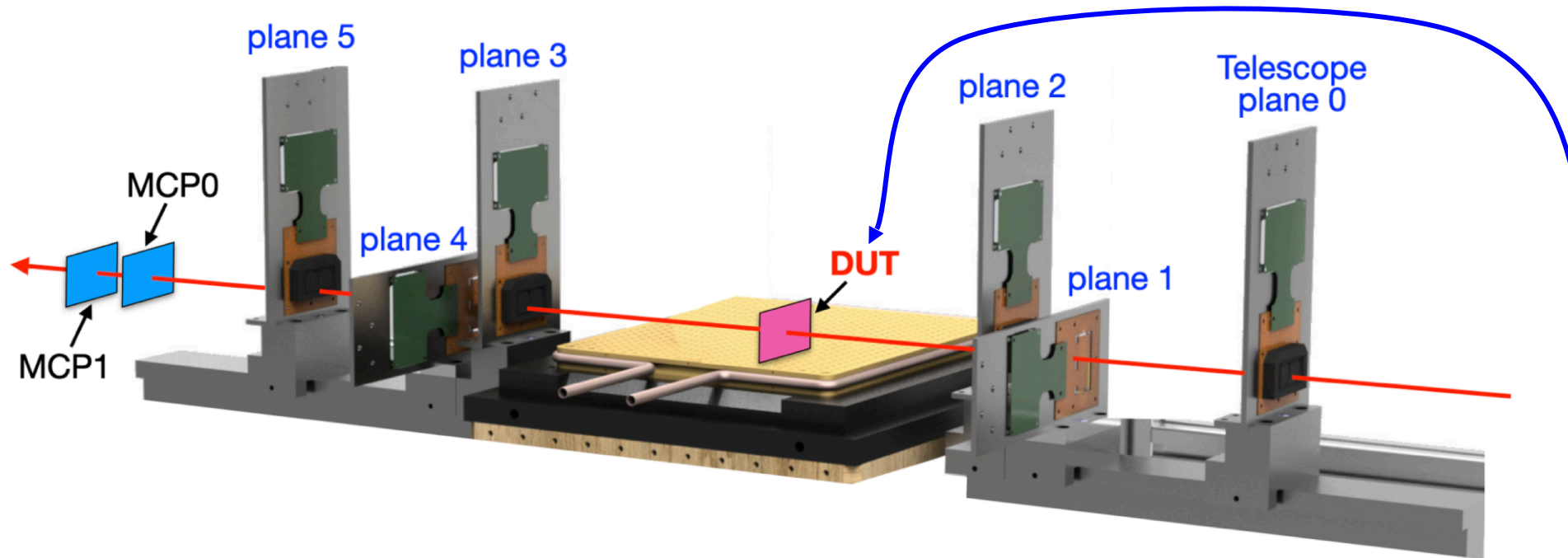
**20 ps**

- Hexagonal pixels 65μm side
- improved electronics
- 50μm epitaxial layer (350Ωcm)



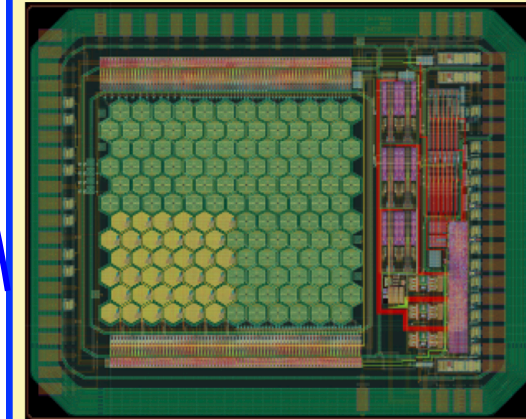


- October 2022: SPS Testbeam with 180 GeV/c pions
- Measure **efficiency** and **time resolution**



**NO GAIN LAYER**

2022

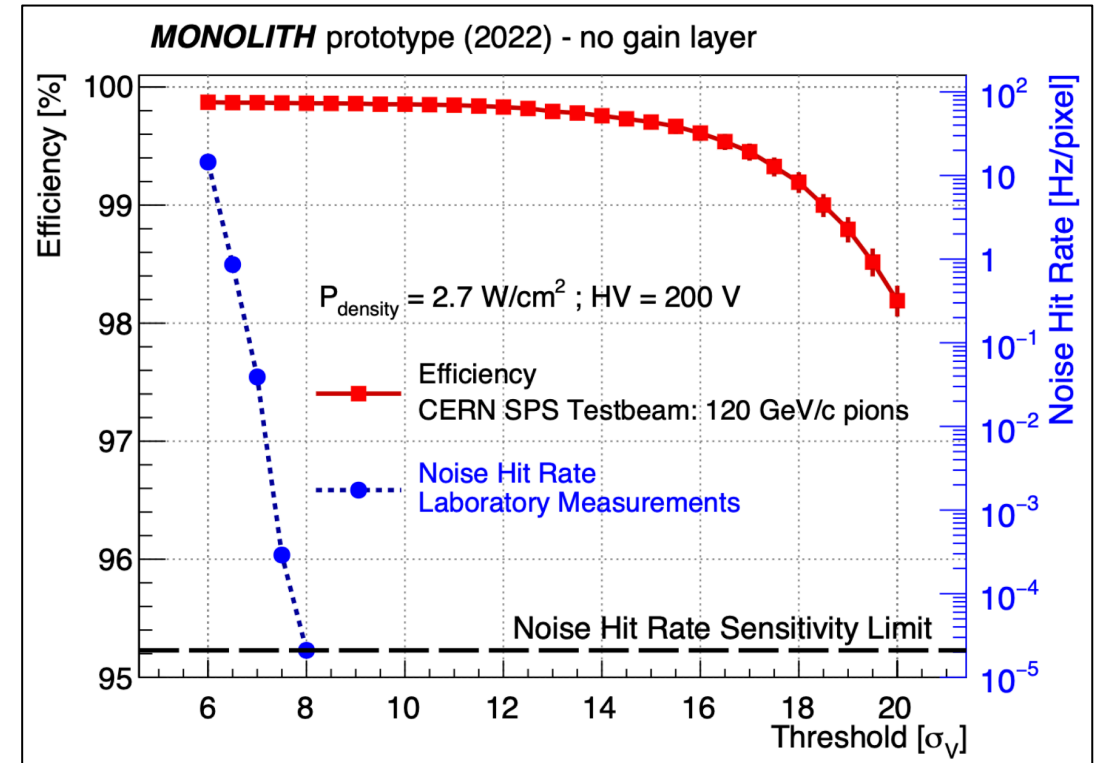
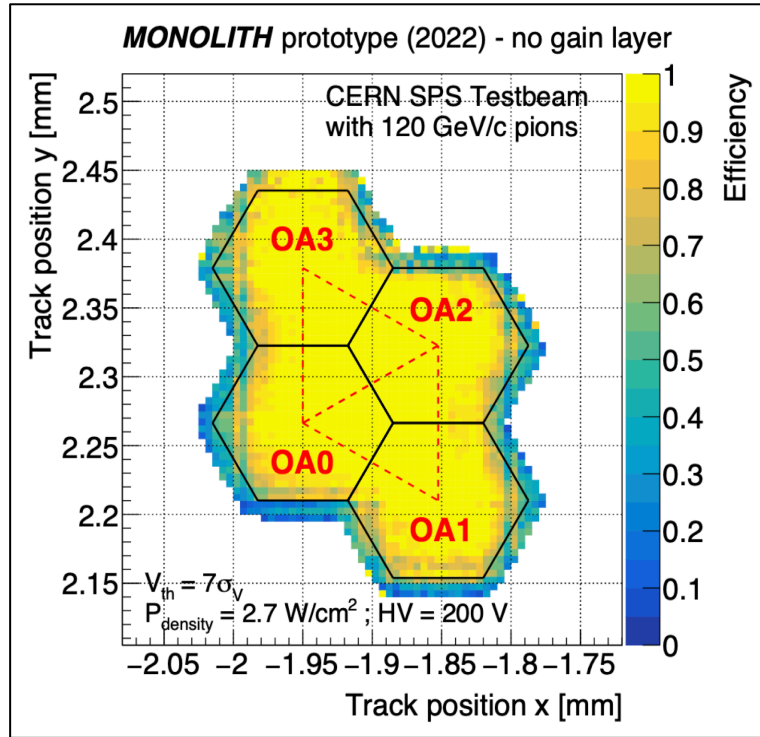


**20 ps**

- Hexagonal pixels 65 $\mu$ m side
- improved electronics
- 50 $\mu$ m epitaxial layer (350 $\Omega$ cm)

- **UNIGE FE-I4 telescope**<sup>[2]</sup> to provide the spatial information ( $\sigma_{x,y} \sim 10 \mu\text{m}$ )
- **Two MCPs** ( $\sigma_t \sim 5 \text{ps}$ ) to provide the timing reference

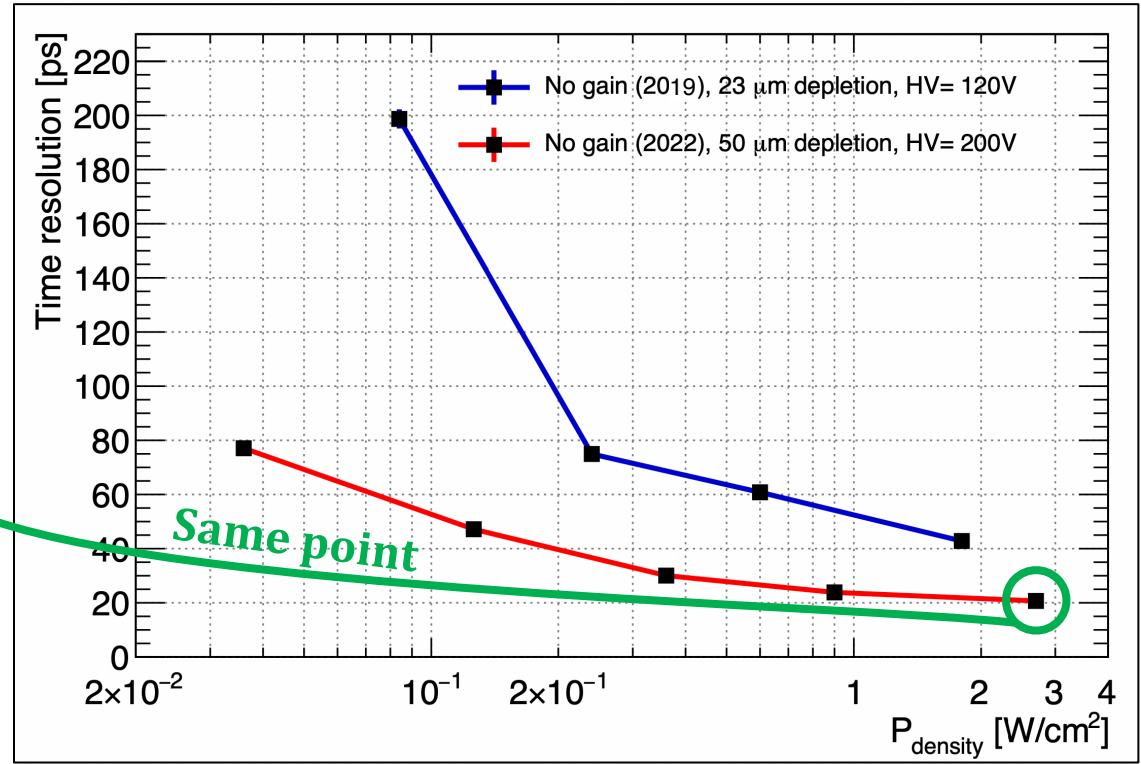
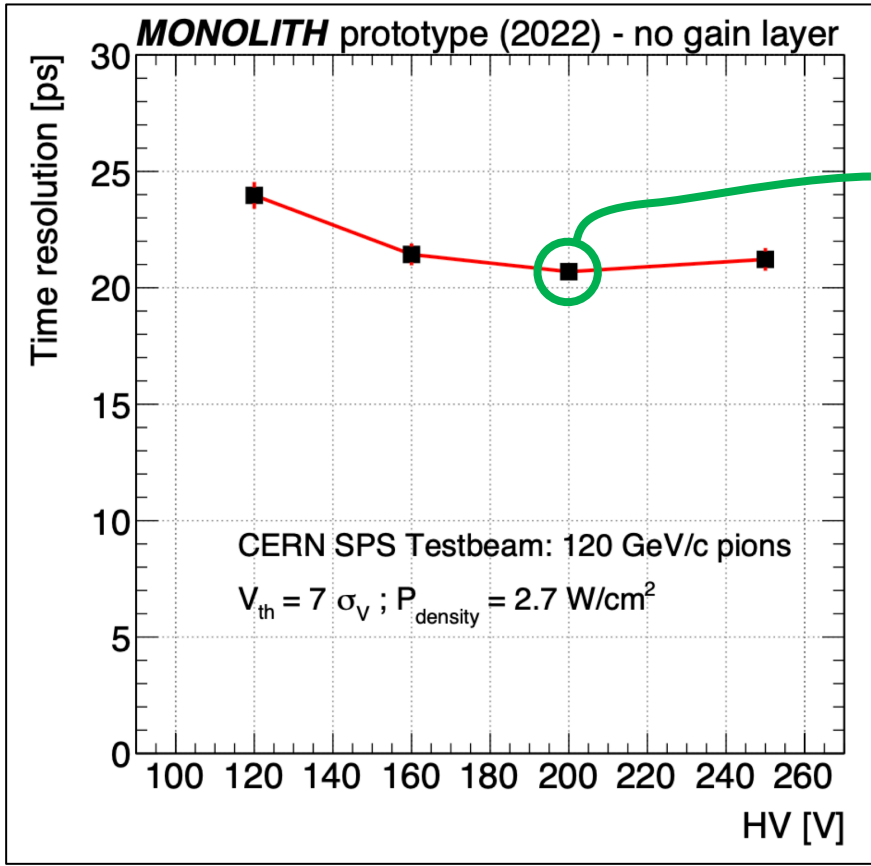
[2]Benoit et al. The FE-I4 telescope for particle tracking in testbeam experiments. JINST, 11 P07003, July 2016



- The **apparent degradation** at the edges is due to the  $\sim 10 \mu\text{m}$  resolution of the telescope
- Selection of two **triangles**:
  - representative of the whole pixel
  - **unbiased** from the telescope resolution

- Large plateau of **99.8% efficiency**
- $\sigma_V \approx 1.4 \text{ mV} \approx 100 e^-$

# Time Resolution Results



Large plateau of 130 V between 20 and 25 ps

- **20 ps at 2.7 W/cm<sup>2</sup> | 50 ps at 0.1 W/cm<sup>2</sup>**
- More than a factor 2 improvement w.r.t. the **previous prototype**

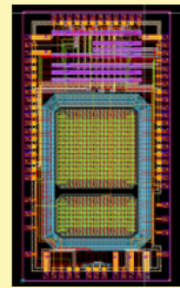


# Monolithic SiGe BiCMOS prototypes



## NO GAIN LAYER

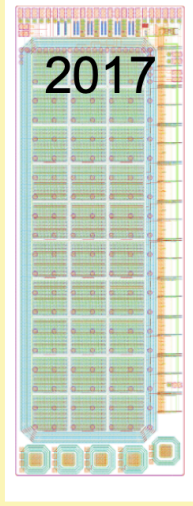
2016



**200 ps**

- 1 mm<sup>2</sup> pixel
- Discriminator

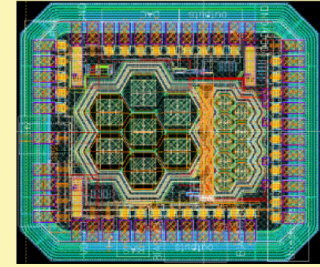
2017



**110 ps**

- 30 pixels 500x500µm<sup>2</sup>
- 100ps TDC +I/O logic

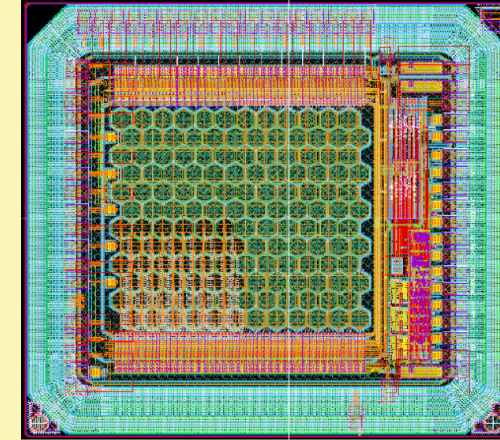
2018



**50 ps**

- Hexagonal pixels 65µm and 130µm side
- Discriminator output

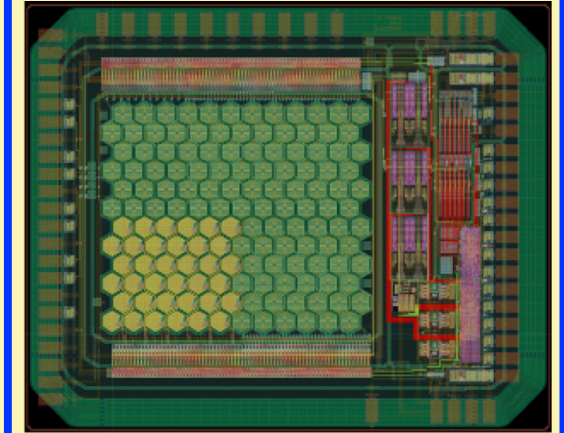
2019



**36 ps**

- Hexagonal pixels 65µm side
- 30ps TDC +I/O logic
- Analog channels

2022



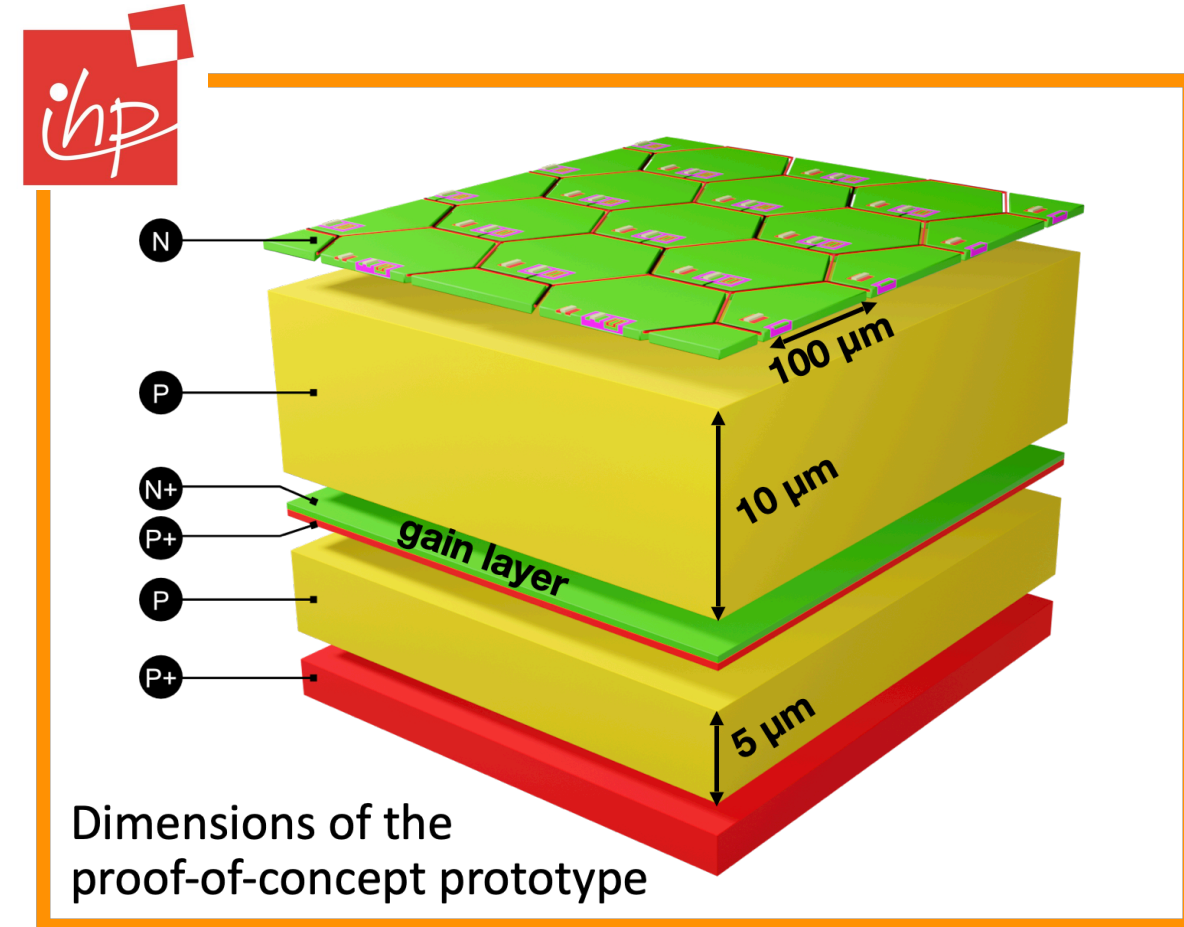
**20 ps**

- Hexagonal pixels 65µm side
- improved electronics
- 50µm epitaxial layer (350Ωcm)



2022  
**PicoAD<sup>®</sup> version**  
**17 ps**

- Multi-Junction **Pico-Avalanche Detector**<sup>[4]</sup>
- 2019 ASIC with the **PicoAD<sup>©</sup> concept**
- Continuous and deep gain layer
  - de-correlation from implant size/geometry  
-> high **pixel granularity** possible  
(enhance spatial resolution)
  - only small fraction of charge gets amplified  
-> **reduced charge collection noise**  
(enhance timing resolution)



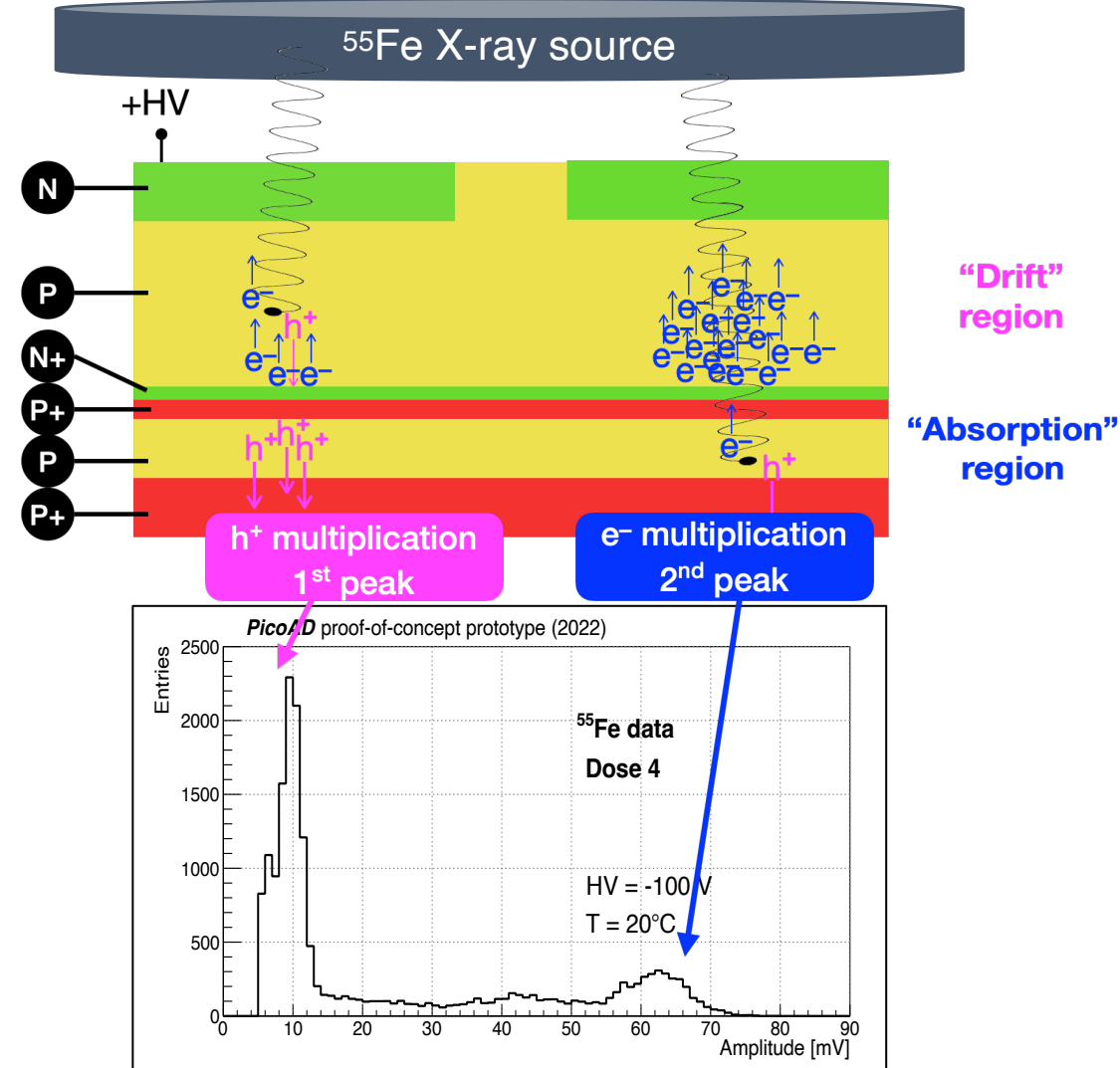
<sup>[4]</sup>G. Iacobucci, L. Paolozzi and P. Valerio. Multi-junction pico-avalanche detector. European Patent EP3654376A1, US Patent US2021280734A1, Nov 2018



- **X-rays from  $^{55}\text{Fe}$  radioactive source**<sup>[5][6]</sup>:
  - mainly  $\sim 5.9$  keV photons
  - point-like charge deposition
- **Characteristic double-peak spectrum**
  - photon absorbed in **drift region**
    - **holes** drift through gain layer and multiplied
    - **first peak** in the spectrum
  - photon absorbed in **absorption region**
    - **electrons** drift through gain layer and multiplied
    - **second peak** in the spectrum
- **Gain up to  $\approx 20$  for  $^{55}\text{Fe}$  X-rays** obtained with HV = -125 V and T = -20 °C

[5]M. Milanesio et al, Gain measurements of the first proof-of-concept PicoAD prototype with a  $^{55}\text{Fe}$  X-ray radioactive source, 2022 doi.org/10.1016/j.nima.2022.167807

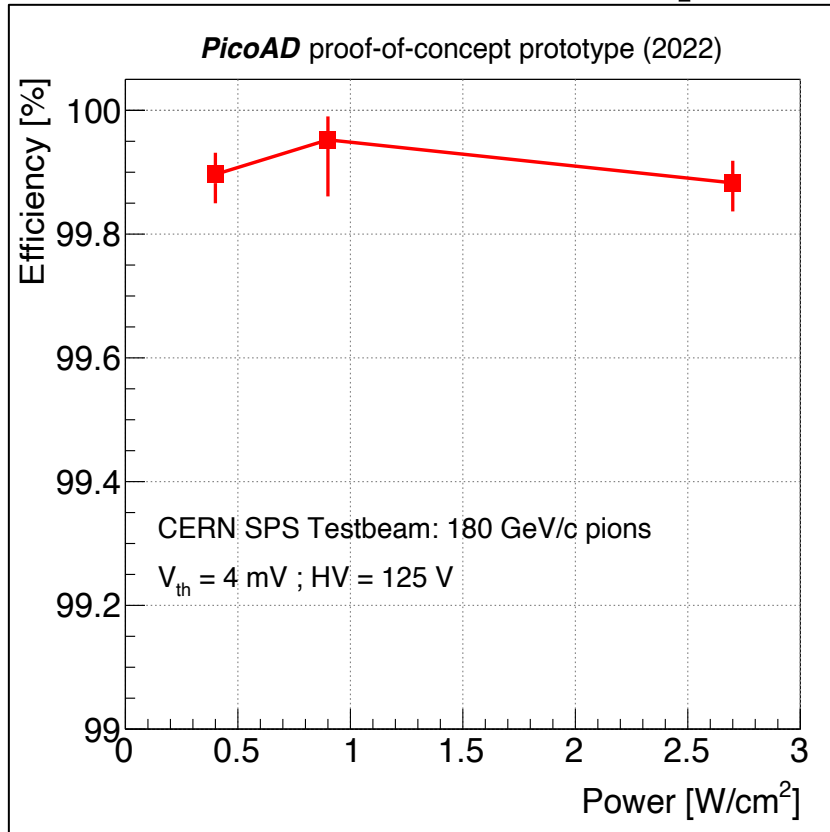
[6]L. Paolozzi et al, Picosecond Avalanche Detector - working principle and gain measurement with a proof-of-concept prototype, 2022 JINST 17 P10032



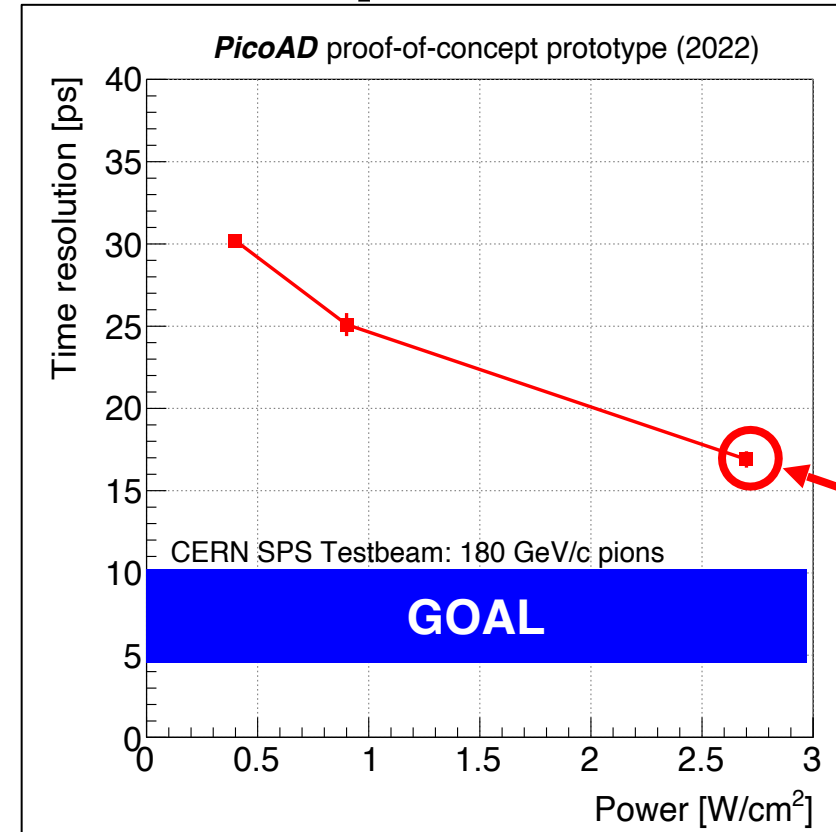
# Efficiency and Time Resolution



Similar experimental setup with FE-I4 telescope



**99.9%** for all the power consumptions



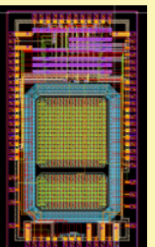
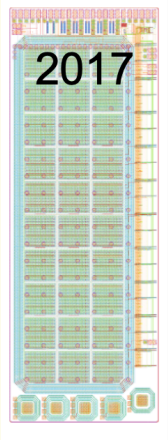
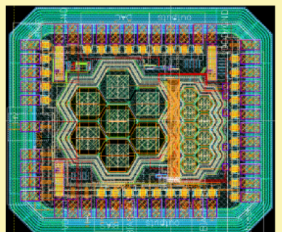
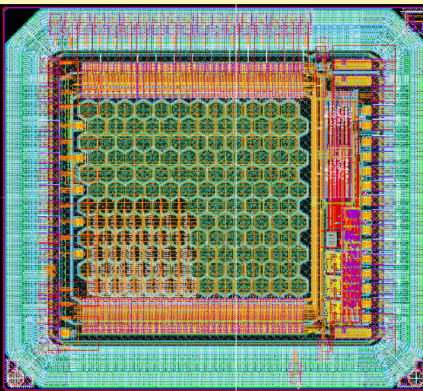
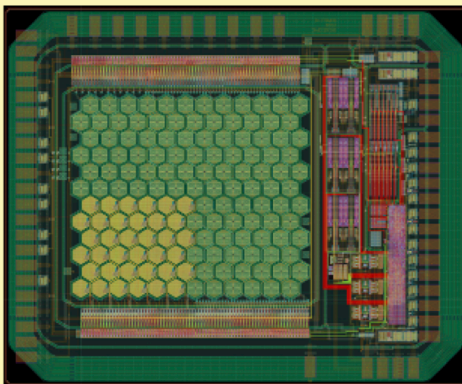
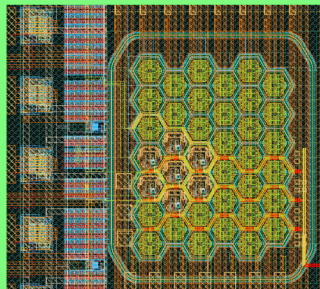
**Best performance<sup>[7]</sup>: (17.3 ± 0.4) ps**  
 HV = 125 V and Power = **2.7 W/cm<sup>2</sup>**

[7] G. Iacobucci et al, Testbeam results of the Picosecond Avalanche Detector proof-of-concept prototype, 2022 JINST 17 P10040

# Future prototypes



## NO GAIN LAYER

<p><b>2016</b></p>  <p><b>200 ps</b></p> <ul style="list-style-type: none"> <li>• 1 mm<sup>2</sup> pixel</li> <li>• Discriminator</li> </ul>	<p><b>2017</b></p>  <p><b>110 ps</b></p> <ul style="list-style-type: none"> <li>• 30 pixels 500x500µm<sup>2</sup></li> <li>• 100ps TDC +I/O logic</li> </ul>	<p><b>2018</b></p>  <p><b>50 ps</b></p> <ul style="list-style-type: none"> <li>• Hexagonal pixels 65µm and 130µm side</li> <li>• Discriminator output</li> </ul>	<p><b>2019</b></p>  <p><b>36 ps</b></p> <ul style="list-style-type: none"> <li>• Hexagonal pixels 65µm side</li> <li>• 30ps TDC +I/O logic</li> <li>• Analog channels</li> </ul>	<p><b>2022</b></p>  <p><b>20 ps</b></p> <ul style="list-style-type: none"> <li>• Hexagonal pixels 65µm side</li> <li>• improved electronics</li> <li>• 50µm epitaxial layer (350Ωcm)</li> </ul>	<p><b>March 2023</b></p>  <p><b>&lt; 20 ps ?</b></p> <ul style="list-style-type: none"> <li>• Hexagonal pixels <b>29µm side</b></li> <li>• improved electronics</li> </ul>
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↓

**2022**  
**PicoAD<sup>©</sup> version**  
**17 ps**

↓

**October 2023**  
**PicoAD<sup>©</sup> version**  
**< 10 ps ?**

# Summary and Outlook



- **Testbeam of 2022 prototype ASIC, without gain layer**, provided:
  - **Efficiency = 99.8%** and  **$\sigma_t = (20.7 \pm 0.3)$  ps**
- **The PicoAD<sup>©</sup> monolithic proof-of-concept prototype works.** The introduction of a deep gain layer improves the performances:
  - **Gain  $\approx 20$**  for <sup>55</sup>Fe X-rays
  - **Efficiency = 99.9 %** including inter-pixel regions
  - **Time resolution  $\sigma_t = (17.3 \pm 0.4)$  ps**
- **Radiation hardness** studies started in 2023 together with KEK and IHP
- Development of **picosecond TDC<sup>[8]</sup>** for fully monolithic chip

[8]R. Cardarelli, L. Paolozzi, P. Valerio and G. Iacobucci, European Patent Application / Filing - UGKP-P-001-EP, Europe Patent EP 18181123.3. 2 July 2018.



# Thanks for your attention



**Giuseppe Iacobucci**  
 • project P.I.  
 • System design



**Lorenzo Paolozzi**  
 • Sensor design  
 • Analog electronics



**Didier Ferrere**  
 • System integration  
 • Laboratory test



**Sergio Gonzalez-Sevilla**  
 • System integration  
 • Laboratory test



**Thanushan Kugathasan**  
 • Lead chip design  
 • Analog electronics



**Mateus Vicente**  
 • System integration  
 • Laboratory test



**Yannick Favre**  
 • Board design  
 • RO system



**Stéphane Débieux**  
 • Board design  
 • RO system



**Roberto Cardella**  
 • Analog electronics  
 • Digital electronics



**Stefano Zambito**  
 • Laboratory test  
 • Data analysis



**Matteo Milanesio**  
 • Laboratory test  
 • Data analysis



**Théo Moretti**  
 • Laboratory test  
 • Data analysis



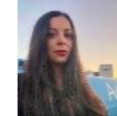
**Antonio Picardi**  
 • Chip design  
 • Firmware



**Chiara Magliocca**  
 • Laboratory test  
 • Data analysis



**Jihad Saidi**  
 • Laboratory test  
 • Data analysis



**Rafaella Kotitsa**  
 • Sensor simulation



**Carlo Alberto Fenoglio**  
 • Chip design  
 • Firmware



**Luca Iodice**  
 • Chip design  
 • Firmware

## Main research partners:



**Roberto Cardarelli**  
 INFN Rome2 & UNIGE



**Holger Rucker**  
 IHP Mikroelektronik



**Marzio Nessi**  
 CERN & UNIGE



**Matteo Elviretti**  
 IHP Mikroelektronik

## Funded by:



**ALSO AT THIS MEETING**



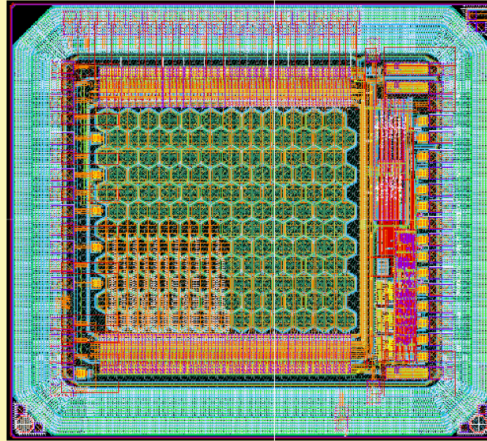
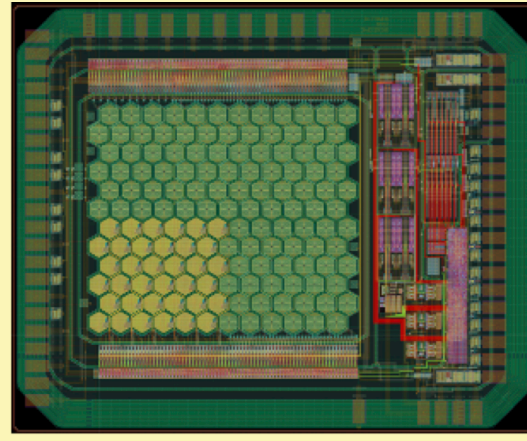


# Backup

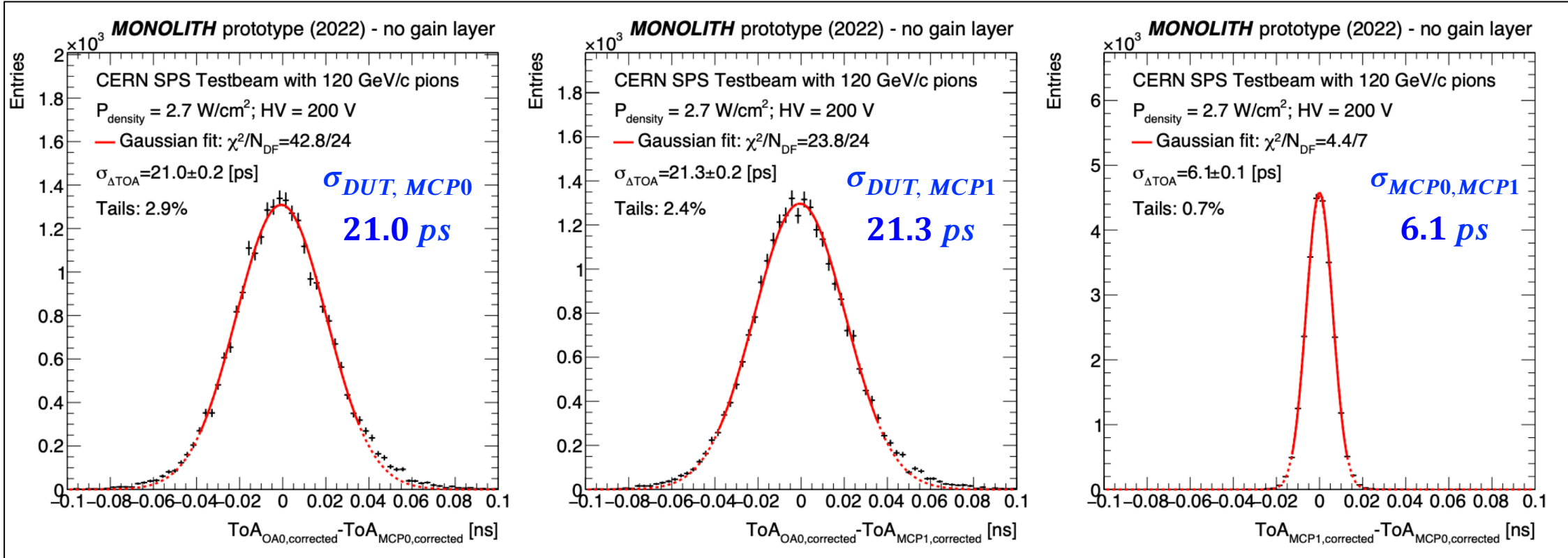
# 2019->2022: Improvements



- Same matrix configuration as previous, but
  - **Substrate:** 50  $\Omega\text{cm}$   $\rightarrow$  350  $\Omega\text{cm}$  epilayer, 50  $\mu\text{m}$  thick on low-res (1  $\Omega\text{cm}$ ) substrate
    - smaller pixel capacitance
    - depletion 23  $\mu\text{m}$   $\rightarrow$  50  $\mu\text{m}$
    - much larger voltage plateau
    - can operate sensor with  $v_{drift}$  saturated everywhere
  - **Preamp and driver** voltage decoupled:
    - was limiting optimal amplifier operation
    - cross-talk removed
  - **Optimised FE layout, “differential” output, high-frequency cables:**
    - better rise time (600 ps  $\rightarrow$  300 ps)

2019	2022
	
<b>36 ps</b>	<b>20 ps</b>
<ul style="list-style-type: none"> <li>• Hexagonal pixels 65<math>\mu\text{m}</math> side</li> <li>• 30ps TDC +I/O logic</li> <li>• Analog channels</li> </ul>	<ul style="list-style-type: none"> <li>• Hexagonal pixels 65<math>\mu\text{m}</math> side</li> <li>• improved electronics</li> <li>• 50<math>\mu\text{m}</math> epitaxial layer (350<math>\Omega\text{cm}</math>)</li> </ul>

# Time Resolution Distributions



- Very **Gaussian** distributions after time walk correction
- Simultaneous fit to extract the time resolution of **DUT, MCP0, MCP1**<sup>[3]</sup>:

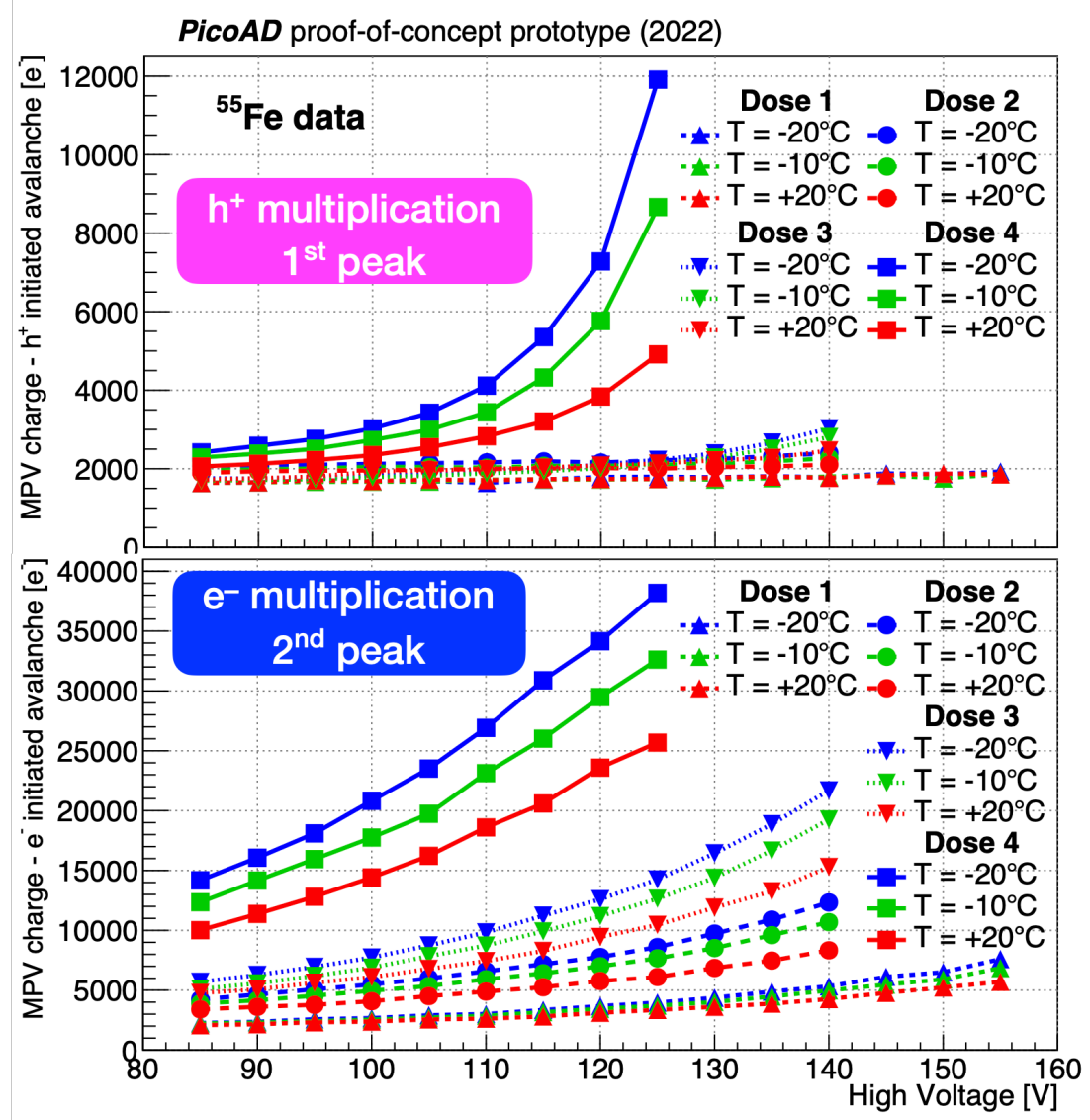
**MCP0:**  $\sigma_t = (3.6 \pm 1.5) \text{ ps}$

**MCP1:**  $\sigma_t = (5.0 \pm 1.1) \text{ ps}$

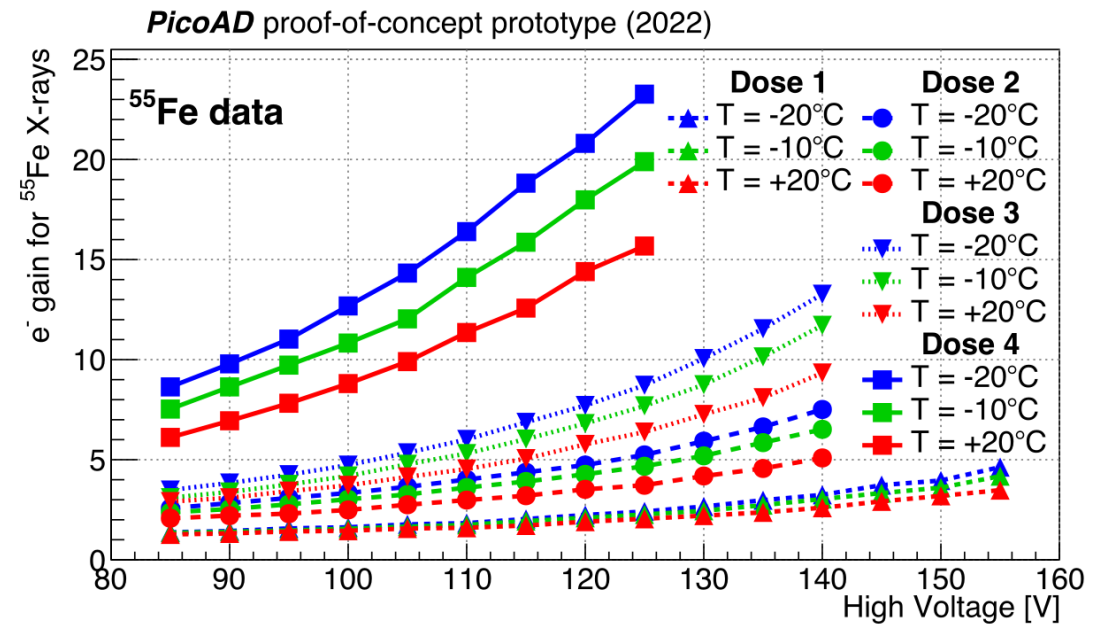
**DUT:**  $\sigma_t = (20.7 \pm 0.3) \text{ ps}$

<sup>[3]</sup>S. Zambito et al. 20 ps Time Resolution with a Fully-Efficient Monolithic Silicon Pixel Detector without Internal Gain Layer. arXiv:2301.12244v1, January 2023

# Gain Results

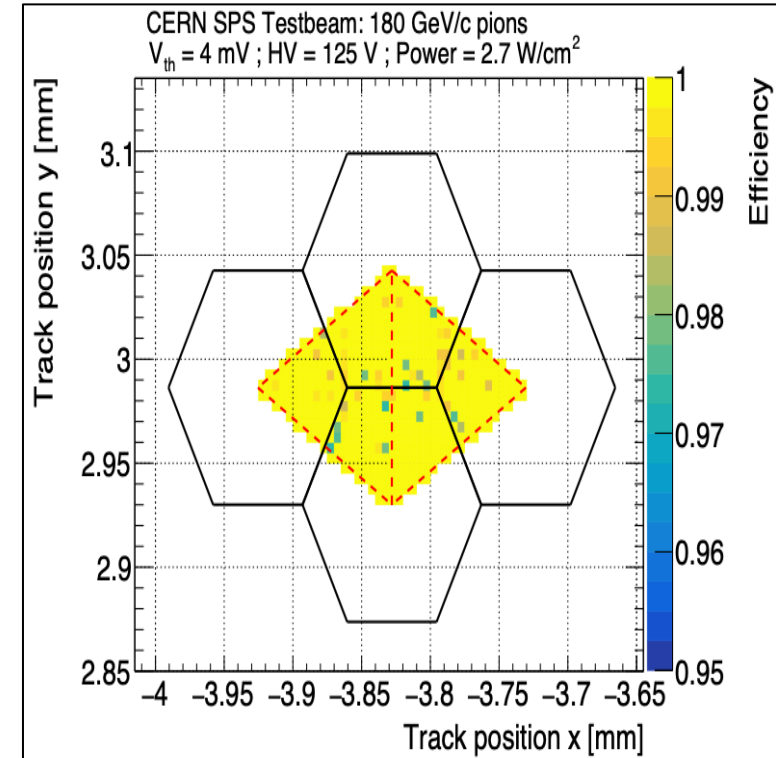
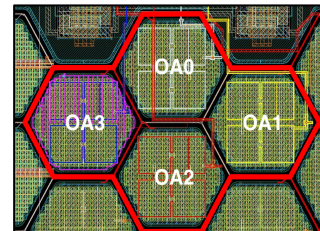
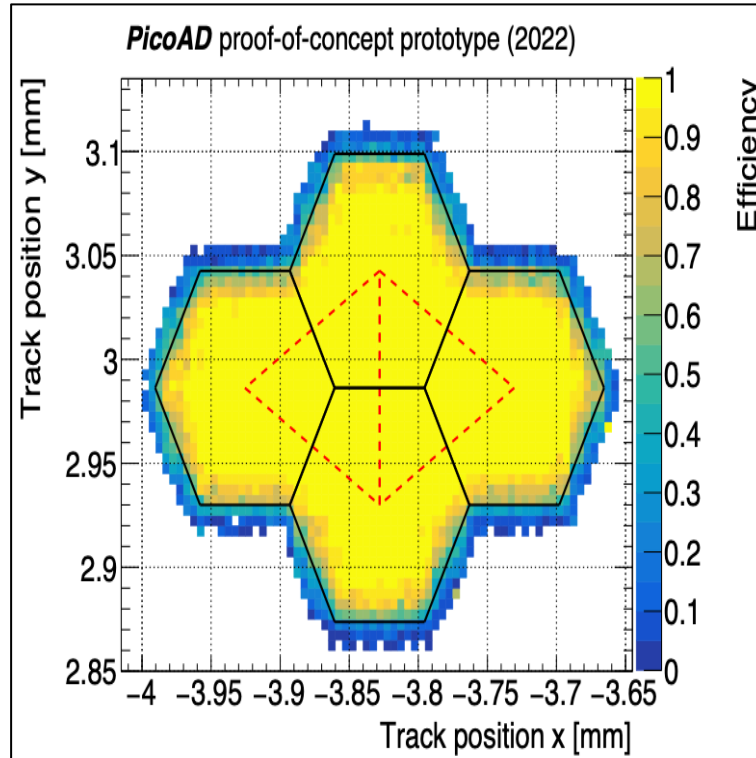


**Gain up to  $\approx 20$  for  $^{55}\text{Fe}$  X-rays**  
obtained at HV = 125 V and T = -20 °C



- Evidence for **gain suppression** due to space-charge effects **in the case of  $^{55}\text{Fe}$  X-rays**
- We estimated that  $^{55}\text{Fe}$  gain of  $\approx 20$  corresponds to **gain 60–70 for a MIP**



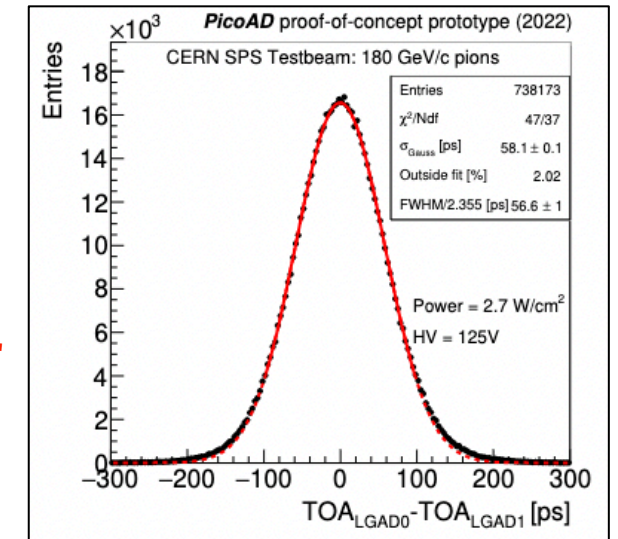
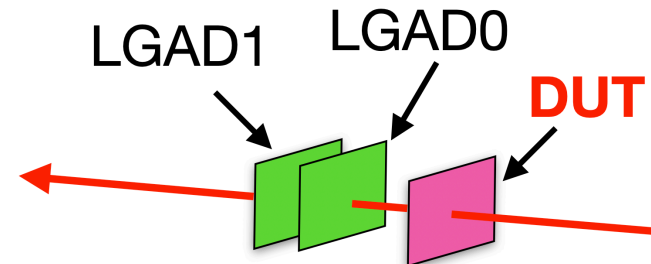
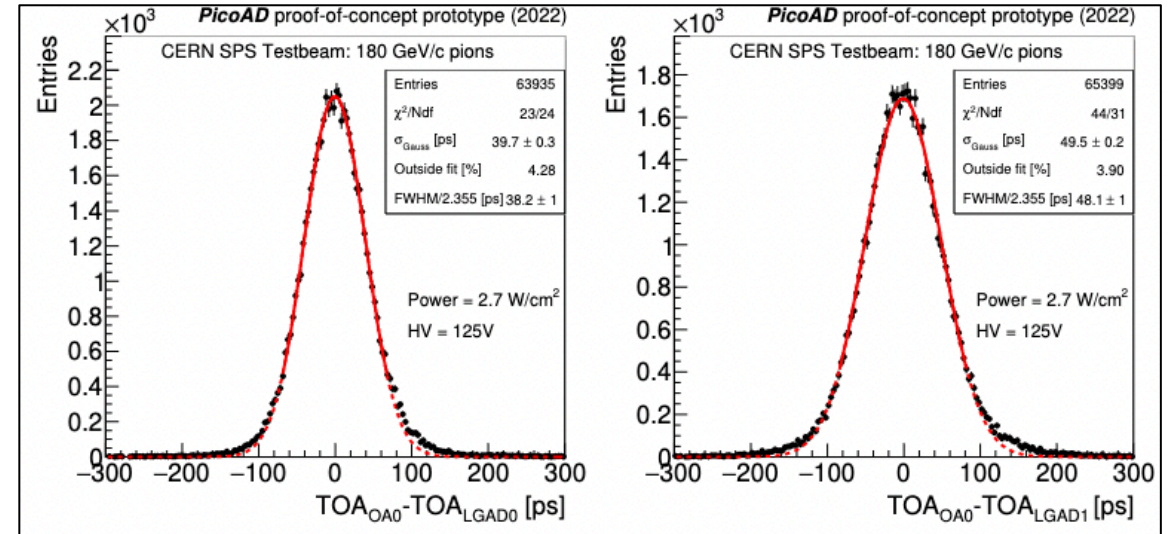


- The **apparent degradation** at the edges is due to the finite resolution of the telescope ( $\sim 10 \mu\text{m}$ )

- Selection of two **triangles**:
  - representative of the whole pixel
  - **unbiased** from the telescope resolution



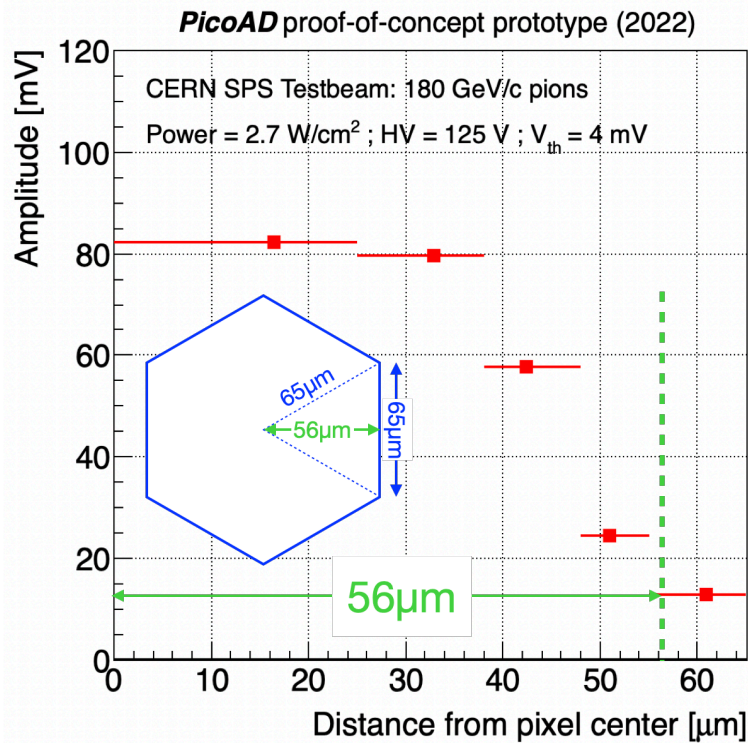
- Time Of Arrival as a time at a Constant Fraction
- Distributions after time-walk correction
- The distributions are **gaussian**
  - ~2-4 % of the entries are in non-gaussian tails
- The three  $\sigma_{Gauss}$  from the fits give the timing resolution of:
  - the DUT
  - the two LGADs



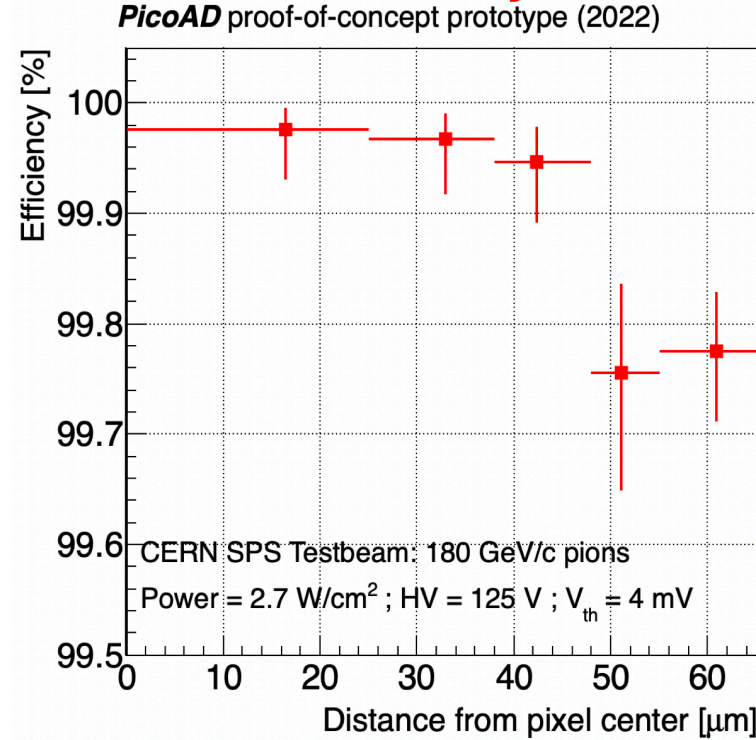
# Position Within the Pixel



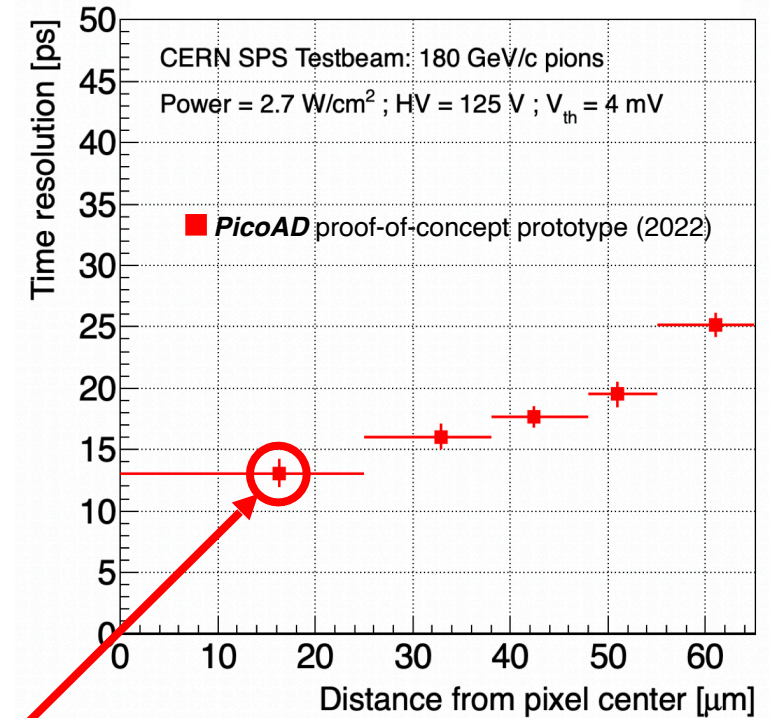
## Signal MPV Amplitude



## Efficiency



## Time Resolution



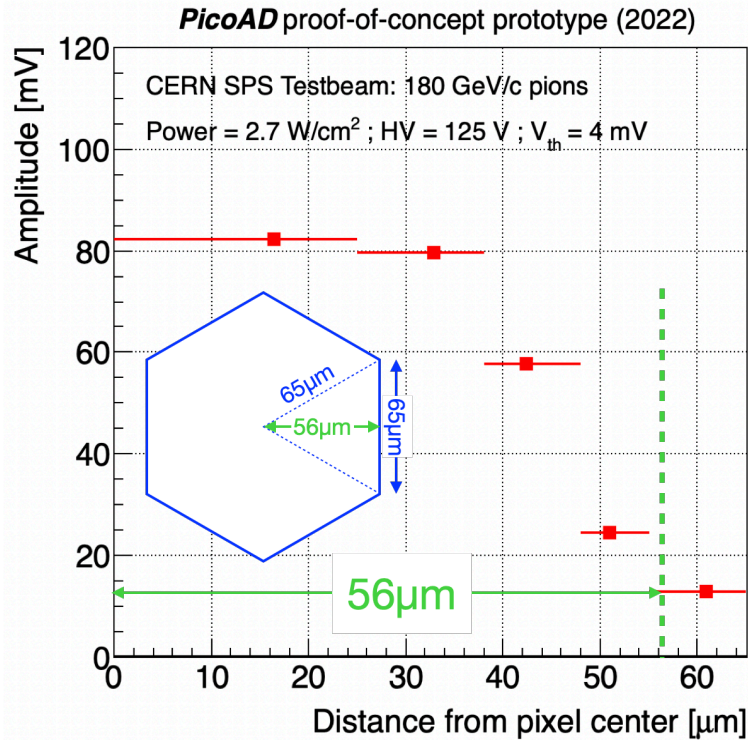
- Best time resolution: **(13.2 ± 0.8) ps within 25 μm** from the pixel center
- **PicoAD**® proof-of-concept: small degradation of the performance towards the edge of the pixel



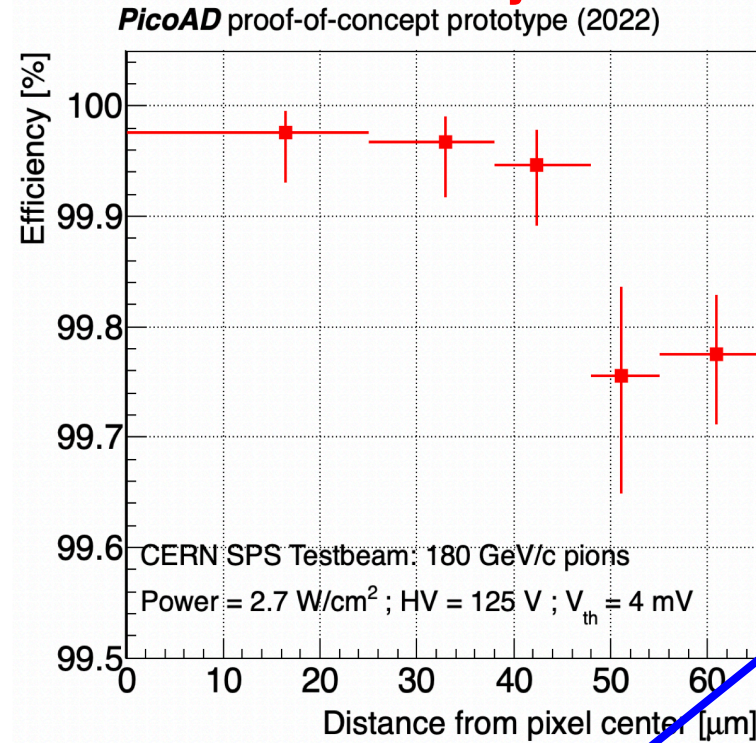
# Position Within the Pixel



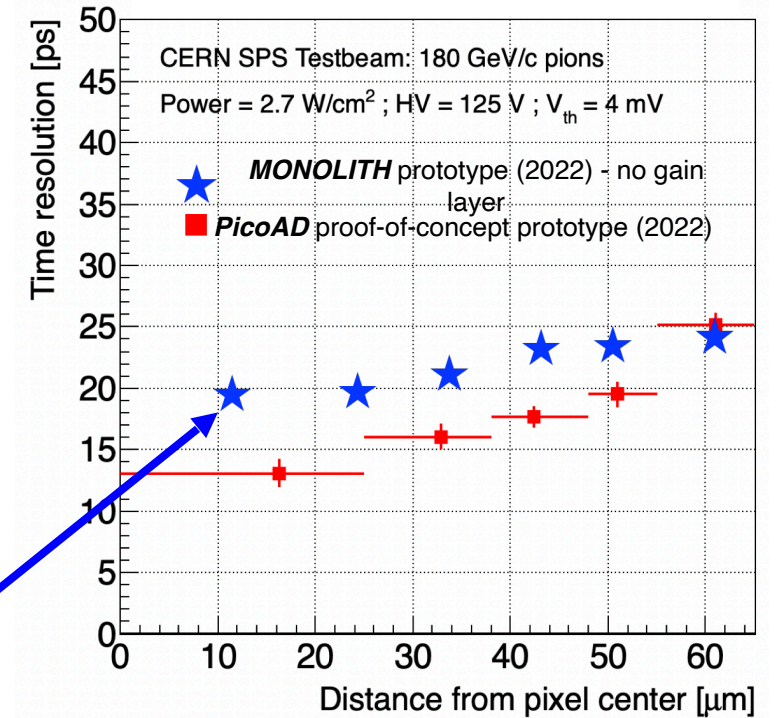
## Signal MPV Amplitude



## Efficiency

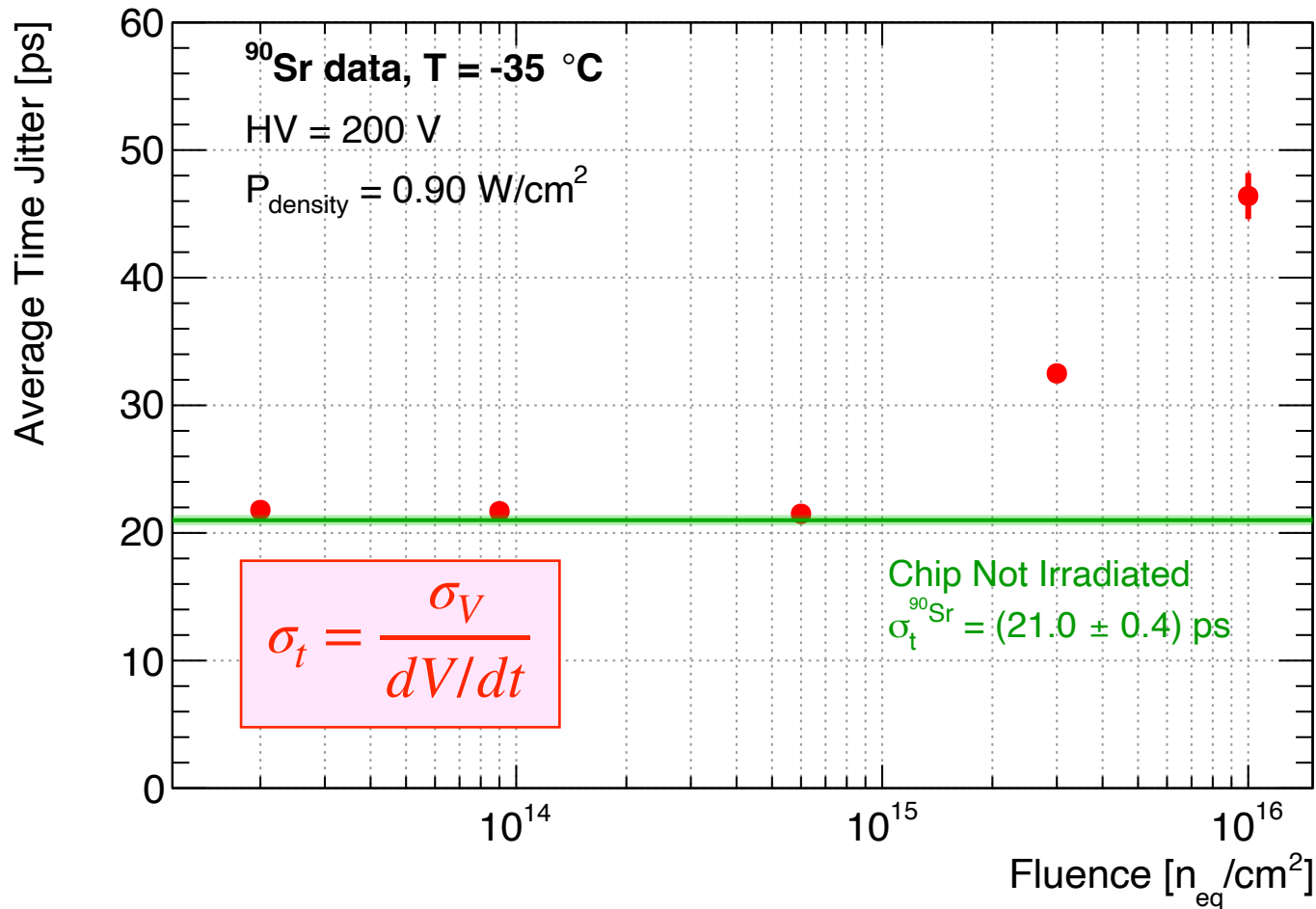


## Time Resolution



2022 prototype is much **less dependent** on the pixel position

**MONOLITH** prototype2 (2022) - no gain layer



Excellent news from radiation tolerance studies:

The time jitter with  $^{90}\text{Sr}$  increases  
**from 21ps** (unirradiated)  
**to 46ps** (at  $10^{16}\text{ n}_{\text{eq}}/\text{cm}^2$ )  
 at **HV = 200V** and **0.9 W/cm<sup>2</sup>**

Enough parameters ( $i_{\text{fbk}}$ ,  $V_{\text{CCA}}$ , HV)  
 for smooth and effective operation  
 even at  $10^{16}\text{ n}_{\text{eq}}/\text{cm}^2$

# Benefits of Using Hexagonal Pixels



- Three possible regular shapes to use:
  - equilateral triangles
  - squares
  - regular hexagons
- Hexagons have the highest angles ( $120^\circ$ ) -> **electric fields** in the corners are better **under control**
- Moreover, the same amount of pixels can fit in less space than squares

